

**INDUSTRY STANDARD OF THE
PEOPLE'S REPUBLIC OF CHINA**

SJ 3244.5-1989

**Methods of measurement for compensation degree of Gallium
arsenide and Indium phosphide materias**

砷化镓和磷化铟材料补偿度的测试方法

(English Translation)

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What this standard covers

This standard specifies the gallium arsenide and indium phosphide material to determine the compensation of the measurement principle, the equipment, the test sample preparation and analysis. This standard applies to the n-type, P-type GaAs and InP epitaxial layer and the high resistance of the substrate, the carrier concentration in the $10^{12} \sim 5 \times 10^{15} \text{ cm}^{-3}$ semiconductor material scope of test and analysis of compensation degree. In principle also applies to the measurement and analysis of other III-V compound material compensation degree.

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